## **HIGH VOLTAGE PUSH-PULL SWITCHING UNITS**

The push-pull switching units of model series GHTS are ready-for-use pulsers and are especially designed for capacitive load elements such as pockels cells, deflection and acceleration grids, ion optics, piezo crystals, pulsed MCP's and SEV's. In combination with an external high voltage power supply and a control signal source true square wave pulses can be generated with amplitudes of 3.000 to 10.000 volts depending on type. The pulsers are galvanically isolated and can therefore be operated in both polarities as well as in different floating modes. The units contain two single switches which are alternately controlled to charge and discharge the capacitive load elements. Due to the absence of working resistors, currents from the H.V. power supply are only drawn to charge the capacitive load. The charge peak current can reach several ten amperes for a few nanoseconds but as soon as the load capacitance is fully charged the output current decreases almost to zero. This guarantees an excellent top flatness regardless to the pulse length. GHTS switching units are carefully optimized regarding all relevant high frequency / high power design aspects and show exceptional good switching characteristics.

The devices consist of a DC/DC converter for the internal driver voltages, a control and protection circuit, a driver circuit and the switching module with the two alternately controlled switches. The switches are made of a large number of series and parallel connected MOSFET. Those MOSFET have intrinsic (parasitic) diodes which appear as parallel diodes at the switch paths. As a result of that the switch polarity is defined. That means when the polarity of input voltage changes the switch polarity must also be changed. This is simply be done by a plug change at the rear panel. Several ceramic capacitors are built-in to provide the necessary charge for fastest transitions and best pulse shape. Insofar a slower switching speed is demanded (e.g. for reduced EMI) or in case the output shall be safely protected against short circuits, the GHTS switching units can be equipped with output series resistors of 200 ohms (standard) or any other resistance value.

The control and protection circuit provides the precise timing of the high voltage switches under all operating conditions. Parameters such as switch temperature, switch control signal amplitude, switching frequency and output peak current are monitorred by the control circuit. Overheating, excessive switching frequency, over current (specific overload cases) and insufficient auxilliary power supply voltage will turn both switches off. Fault and switch condition are displayed by LED's. By means of a switchable inverter the control signal can be negated simply if necessary. A capacitively coupled monitoring output is provided to verify the high voltage pulses. Control input and trigger output are compatible to the TTL signal level (Z=50).

The GHTS switching units are built into small metal flange housings for ease of installation near the load element to be switched. This offers the advantage of a short pulse transmission cable with low capacitance which is the precondition for short transition times and low power losses at high switching frequencies. All connections are made by standard plug-in connectors. A complete set of plugs and adaptors is supplied with the unit. For operation at higher frequencies and higher capacitances an optional fan is available for some models (see data table overleaf).

## GHTS 30 GHTS 60 GHTS 100

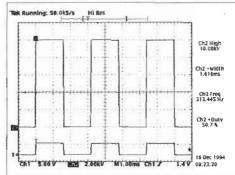
3000 VDC, 30-60 Amps

6000 VDC, 15-60 Amps

10000 VDC, 15-30 Amps



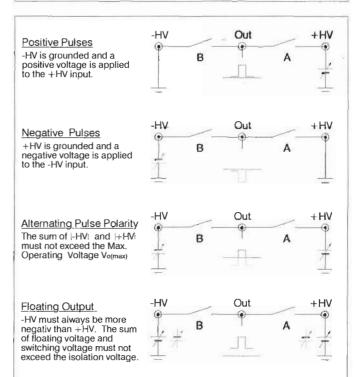
- True square wave pulses
- Nanoseconds rise time
- Low over and undershoot
- Highly stable pulse top
- No working resistor power
- Galvanic isolation
- Pulse monitor outputIsolated trigger output
- Switchable signal inverter
- H.V. plug-in connectors



## Wave Shape

The high voltage output signal (Ch 2) corresponds exactly to the input control signal (Ch 1). The pulse top flatness is determined by the accuracy and ripple of the externally connected H.V. power supply only.

CH2 vertical: 2 kV/div Horizontal: 1ms/div. Pure capacitive load



Weight	Dimensions	Avalanche Strength of Switch	Short-Circuit Strength and	Trigger Output Voltage	Control Signal Voltage	Auxiliary Supply Current	Auxiliary Supply Voltage	Diode Forward Voltage Drop ③	Diode Reverse Recovery Time ③	Total Switch Capacitance	Temperature Range	Linear Derating	Max. Cont. Power Dissipation @	(Number of pulses per burst)	Burst Capability	Maximum Burst Frequency	Maximum Switching Frequency	Typical Turn-On Jitter	Switch Recovery Time	Maximum Pulse Width	Minimum Pulse Width			(Output Rise & Fall Time)	Typical Transition Time	Pulse Delay Time	Quiescent Current	Static On-Resistance	Max. Continuous Load Current	Maximum Peak Current	Galvanic Isolation	Max. Operating Voltage Range®	Specification
				Vtr(out)	Va	Jaux	Vaux	V <sub>F</sub>	trrc	Cs	To		P <sub>d(max)</sub>			f <sub>b(mex)</sub>	f <sub>(max)</sub>	t <sub>j(on)</sub>	trc	ton(max)	ton(min)				t <sub>r(on)</sub>	t <sub>d(on)</sub>	off	R <sub>stat</sub>	L(max)	lP(max)	<	VO(max)	Symbol
Complete set	LxWxH, Case body only	is provided for all models	An active basis protection	Output isolated, short circuit proof,	> 3VDC recommended	Standard devices / (Option 02 - fans)	Supplied from plug-in mains adapter	$l_F = 0.1 \times l_{P(max)}$	$l_F = 0.1 \times l_{P(max)}$	Natural & parasitic		Above 25°C, standard	$T_{case} = 25$ °C, s				Please note possible Pd(max) limitations	$V_{tr} = 5.0 \text{ VDC}$	t <sub>rc</sub> = minimum					10-90 %	0.5 x V <sub>O(max)</sub>	$C_L = 0 pF, 50$	Caused by internal safety discharge resistor	Standard devices at 0.1 x lp(max)	T <sub>case</sub> = 25°C, Standard devices / (Opt. 01)	$T_{case} = 25$ °C, $t_p < 10 \mu s$ , duty cycle $< 1 \%$	Switches against		Candition / Comment
	ody only	all models	protection	, short circuit	nmended	es / (Option (	plug-in mains a	0		sitic capacitances,		tandard devices /	standard devices /	Pul	At the minim		ssible P <sub>d(max)</sub> lir		minimum pulse spacing			Opt. 01 (+200Ω),				50-50 %	rnal safety disc	es at 0.1 x lp(m	tandard device	< 10 \(\mu \text{s}\), duty	st GND (continuously)		Comment
	The state of the s	With option 01	Standard devices	proof, $Z = 50\Omega$		02 - fans)	dapter			ces, see note ②		es / (Opt. 02)	s / (Opt. 02)	Pulse spacing > 1µs	At the minimum pulse spacing		nitations ②					00ಬ), C <sub>L</sub> ್=100 pF	$C_L = 500 pF$	$C_{L} = 100  pF$	$C_L = 25 pF$		charge resistor	lax)	s / (Opt. 01)	cycle <1%	nuously)		
		+++++++++	+ + +					4		75		0.6	15	> 1000	> 200	4	20	100	250		100	34	46	20	12	100	25	50		30		0-3000	30
2.0	170 x 110 x 45	+++++++++++++++++++++++++++++++++++++++	+ + + +					3.5		110		0.6	15	> 500	> 100	3.3	15	300	300		150	30	26	14	10	110	25	50		60	i	0-3000	30 A
		+++++	+++					4		75		0.6	15	>1000	> 200	4	20	100	250	No limit, pu	100	62	105	38	15	100	50	75		15		0-6000	60
		+++++	+ + +	4	2-10	300 (500)	12 (±10%)	6.5	-	100	-4050	0.8 (1.6)	20 (40)	> 750	> 150	4	20	100	250	No limit, pulse width up to DC possible	100	35	49	21	12	100	50	50	200 (100)	30	> 10000	0-6000	60 A
2	210 x 1	+ + + + + +	+ + + +					6		140		0.8 (1.6)	20 (40)	>500	>100	3.3	15	300	300	DC possible	150	31	28	15	10	110	50	50		60		0-6000	60 B
2.5	210 x 110 x 45	++	+					6.5		100		0.8 (1.6)	20 (40)	>750	>150	3.3	15	300	300		100	65	106	43	15	110	80	90		15		0-10000	100
		++++	++					6		140		0.8 (1.6)	20 (40)	>500	>100	3.3	15	300	300		150	50	68	30	14	110	80	75		30		0-10000	100 A
g	mm <sup>3</sup>			VDC	VDC	mADC	VDC	VDC	μs	pF	°C	W/K	Watts	Pulses	z	MHz	kHz	ps	ns		ns	ns				ns	μADC	Ω	mADC	ADC	VDC	VDC	Unit

① Floating and bipolar configurations: The sum of the absolute values [+HV] and [-HV] must not exceed Volmant.

Ordering Informations	
GHTS	Push-Pull Switching Unit
Option 01	Protective Series resistors
Option 02	Built-in miniature fans

② Capacitive power dissipation is determined by the equation  $P_d = V_0^2 \cdot f \cdot (C_L + C_S)$  whereby Vo is the operating voltage, f the switching frequency,  $C_L$  the load capacitance and  $C_S$  the switch capacitance.

<sup>3</sup> Parasitic MOSFET diodes must not be operated dynamicly. Please consult factory in case of inductive load or current reversal.